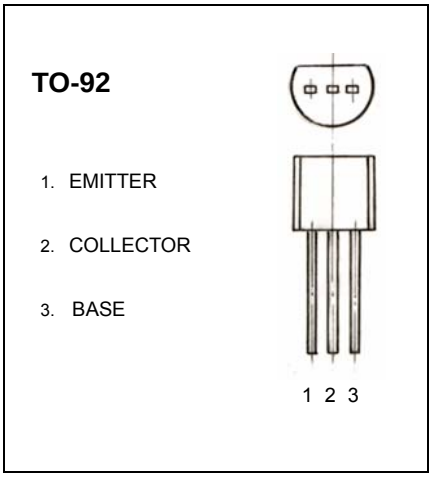
SHENZHEN HAOCHANG SEMICONDUCTOR CO.,LTD.

TO-92 Plastic-Encapsulate Transistors

2SC388 TRANSISTOR (NPN)



FEATURES

TV final pictureif amplifier applications

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Emitter Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	4	V
I_C	Collector Current -Continuous	50	mA
Pc	Collector Power dissipation	300	mW
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=10μA,I_E=0	30			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=5mA,I_B=0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA,I_C=0	4			V
Collector cut-off current	I_{CBO}	V_{CB}=30V,I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=3V,I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=12.5V,I_C=12.5mA	20		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=15mA,I_B=1.5mA			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=15mA,I_B=1.5mA			1.2	V
Transition frequency	f_T	V_{CE}=12.5V,I_C=12.5mA	300			MHz
Collector output capacitance	C_{ob}	V_{CB}=10V,I_E=0,f=1MHz	0.8		2	pF
Power Gain	Gpe	V_{CC}=12.5V,I_E=-12.5mA, f=45MHZ	28		36	dB